DISCRETE SEMICONDUCTORS



Product specification Supersedes data of July 1991 1996 Mar 20



BAT81; BAT82; BAT83

Schottky barrier diodes

FEATURES

- Low forward voltage
- High breakdown voltage
- Guard ring protected
- Hermetically-sealed leaded glass
 package
- Low diode capacitance.

APPLICATIONS

- Ultra high-speed switching
- Voltage clamping
- Protection circuits
- Blocking diodes.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|------------------|-------------------------------------|---------------------------------------|------|------|------|
| V _R | continuous reverse voltage | | | | |
| | BAT81 | | _ | 40 | V |
| | BAT82 | | - | 50 | V |
| | BAT83 | | - | 60 | V |
| l _F | continuous forward current | | - | 30 | mA |
| I _{FRM} | repetitive peak forward current | $t_p \le 1 \text{ s}; \delta \le 0.5$ | _ | 150 | mA |
| I _{FSM} | non-repetitive peak forward current | $t_p \le 10 \text{ ms}$ | - | 500 | mA |
| T _{stg} | storage temperature | | -65 | 150 | °C |
| Tj | junction temperature | | - | 125 | °C |

DESCRIPTION

Planar Schottky barrier diode with an integrated protection ring against static discharges, encapsulated in a hermetically-sealed subminiature SOD68 (DO-34) package. The diode is suitable for mounting on a 2 E (5.08 mm) pitch.



Fig.1 Simplified outline (SOD68; DO-34), pin configuration and symbol.

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ELECTRICAL CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MAX. | UNIT |
|----------------|-------------------|---|------|------|
| V _F | forward voltage | see Fig.2 | | |
| | | I _F = 0.1 mA | 330 | mV |
| | | I _F = 1 mA | 410 | mV |
| | | I _F = 15 mA | 1 | V |
| I _R | reverse current | $V_R = V_{Rmax}$; see Fig.3 | 200 | nA |
| C _d | diode capacitance | $f = 1 \text{ MHz}; V_R = 1 \text{ V}; \text{ see Fig.4}$ | 1.6 | pF |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|---------------------|---|------------|-------|------|
| R _{th j-a} | thermal resistance from junction to ambient | note 1 | 320 | K/W |

Note

1. Refer to SOD68 standard mounting conditions.

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GRAPHICAL DATA





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PACKAGE OUTLINE



DEFINITIONS

| Data sheet status | | |
|---|---|--|
| Objective specification | cification This data sheet contains target or goal specifications for product development. | |
| Preliminary specification | This data sheet contains preliminary data; supplementary data may be published later. | |
| Product specification | This data sheet contains final product specifications. | |
| Limiting values | | |
| more of the limiting values r of the device at these or at a | accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or may cause permanent damage to the device. These are stress ratings only and operation any other conditions above those given in the Characteristics sections of the specification imiting values for extended periods may affect device reliability. | |
| Application information | | |
| Whore application informati | on is given, it is advisory and does not form part of the specification. | |

LIFE SUPPORT APPLICATIONS

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